

ZVP4424G

SOT223 P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Features and Benefits

- 240 Volt VDS
- R_{DS(on)}= 8.8W typical at VGS=-3.5V
- Low Threshold and Fast Switching
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

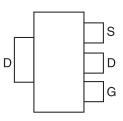
- Electronic Hook Switches
- Telecoms and Battery Powered Equipment

Mechanical Data

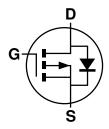
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish@3
- Weight: 0.112 grams (Approximate)







Pin Out - Top



Equivalent Circuit

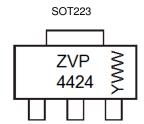
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVP4424GTA	ZVP4424	7	8	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZVP4424 = Product Type Marking Code YWW = Date Code Marking Y or Y = Last Digit of Year (ex: 5= 2015) WW or WW = Week Code (01~53)



ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-240	V
Gate-Source Voltage	V _{GSS}	±40	V
Continuous Drain Current (@ T _A =+25 °C)	I _D	-480	mA
Pulsed Drain Current	I _{DM}	-1.0	Α
Power Dissipation (@ T _A =+25 °C)	P _D	2.5	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	℃

ELECTRICAL CHARACTERISTICS (@ T_A = +25 °C, unless otherwise stated.)

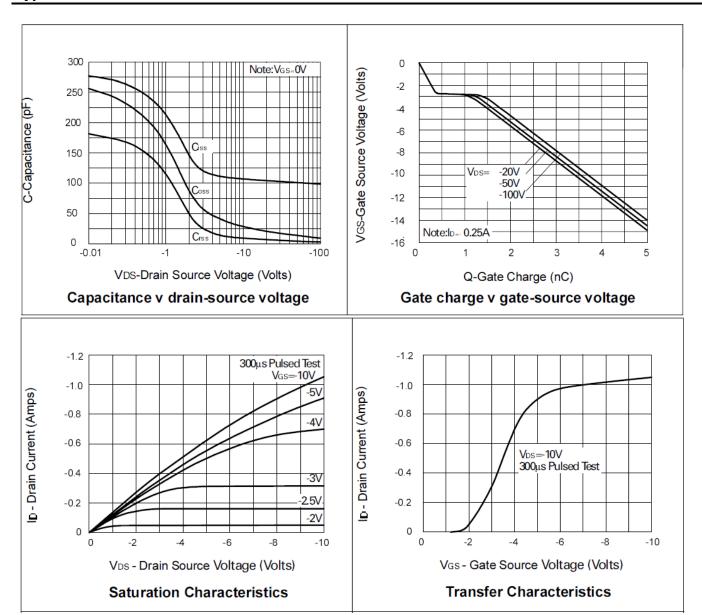
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-240	-	-	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current T _J = +25℃	I _{DSS}	-	-	-10 -100	μA μA	V _{DS} = -240V, V _{GS} = 0V V _{DS} = -190V, V _{GS} = 0V, T _A =+125℃	
Gate-Source Leakage	I _{GSS}	-	-	100	nA	$V_{GS} = \pm 40V$, $V_{DS} = 0V$	
On-State Drain Current	I _{D(ON)}	-0.75	-1.0	-	Α	$V_{GS} = -10V, V_{DS} = -10V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-0.7	-1.4	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	-	7.1 8.8	9 11	Ω	$V_{GS} = -10V, I_D = -200mA$ $V_{GS} = -3.5V, I_D = -100mA$	
Forward Transconductance (Notes 5 & 6)		125	-	-	mS	V _{DS} = -10V, I _D = -0.2A	
DYNAMIC CHARACTERISTICS (Note 6)	, , ,						
Input Capacitance	C _{iss}	-	100	200	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	18	25	pF		
Reverse Transfer Capacitance	C _{rss}	-	5	15	pF		
Turn-On Delay Time (Note 7)	t _{D(ON)}	-	8	15	ns		
Turn-On Rise Time (Note 7)	t _R	-	8	15	ns	$V_{DD} \approx -50V, I_D = -0.25A,$	
Turn-Off Delay Time (Note 7)	t _{D(OFF)}	-	26	40	ns	V _{GEN} = -10V	
Turn-Off Fall Time (Note 7)	t _F	-	20	30	ns		

^{5.} Measured under pulsed conditions. Width=300ms. Duty cycle ≤ 2%.

^{6.} Sample test.
7. Switching times measured with 50Ω source impedance and <5ns rise time on a pulse generator spice parameter data is available upon request for this device.



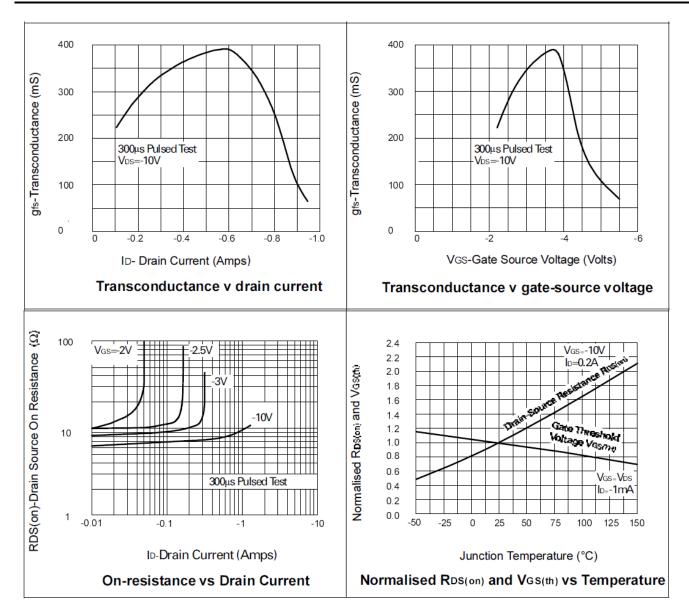
Typical Characteristics



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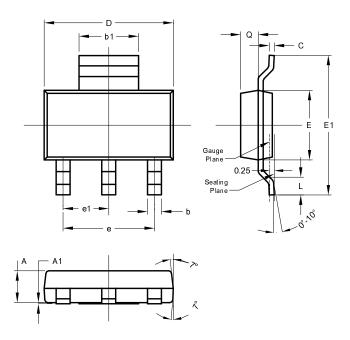
Typical Characteristics (continued)





Package Outline Dimensions

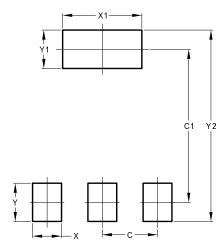
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
V2	8 00



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